

# DATA SHEET

## **PDTA143Z series**

PNP resistor-equipped transistors;

R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

Product data sheet  
Supersedes data of 2003 Sep 08

2004 Aug 05

# PNP resistor-equipped transistors; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$

## PDTA143Z series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	–50	V
I <sub>O</sub>	output current (DC)	–	–100	mA
R1	bias resistor	4.7	–	k $\Omega$
R2	bias resistor	47	–	k $\Omega$

### DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA143ZE	SOT416	SC-75	37	PDTC143ZE
PDTA143ZEF	SOT490	SC-89	52	PDTC143ZEF
PDTA143ZK	SOT346	SC-59	19	PDTC143ZK
PDTA143ZM	SOT883	SC-101	DP	PDTC143ZM
PDTA143ZS	SOT54 (TO-92)	SC-43	TA143Z	PDTC143ZS
PDTA143ZT	SOT23	–	*19 <sup>(1)</sup>	PDTC143ZT
PDTA143ZU	SOT323	SC-70	*47 <sup>(1)</sup>	PDTC143ZU

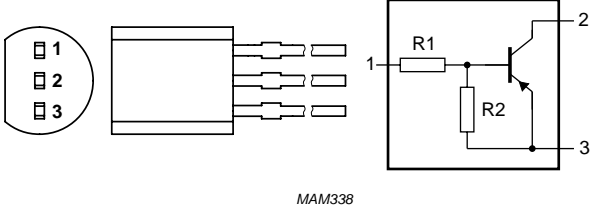
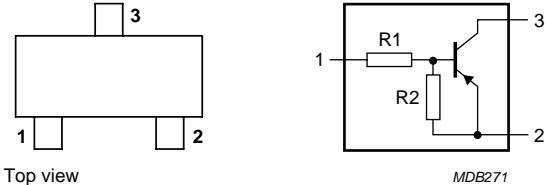
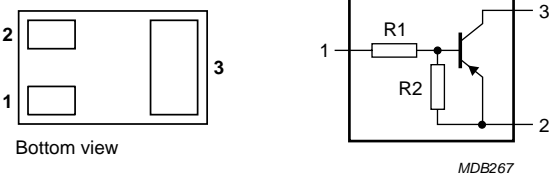
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

PNP resistor-equipped transistors;  
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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA143ZS		1 2 3	base collector emitter
PDTA143ZE PDTA143ZEF PDTA143ZK PDTA143ZT PDTA143ZU		1 2 3	base emitter collector
PDTA143ZM		1 2 3	base emitter collector

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### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–10	V
V <sub>I</sub>	input voltage				
	positive		–	+5	V
	negative		–	–30	V
I <sub>O</sub>	output current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT23	note 1	–	250	mW
	SOT54	note 1	–	500	mW
	SOT323	note 1	–	200	mW
	SOT346	note 1	–	250	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT23	note 1	500	K/W
	SOT54	note 1	250	K/W
	SOT323	note 1	625	K/W
	SOT346	note 1	500	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

### Notes

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## CHARACTERISTICS

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0	–	–	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0	–	–	-1	$\mu$ A
		V <sub>CE</sub> = -30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	-50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0	–	–	-170	$\mu$ A
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -10 mA	100	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -5 mA; I <sub>B</sub> = -0.25 mA	–	–	-100	mV
V <sub>i(off)</sub>	input-off voltage	I <sub>C</sub> = -100 $\mu$ A; V <sub>CE</sub> = -5 V	–	-0.6	-0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = -5 mA; V <sub>CE</sub> = -0.3 V	-1.3	-0.9	–	V
R1	input resistor		3.3	4.7	6.1	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		8	10	12	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = -10 V; f = 1 MHz	–	–	3	pF

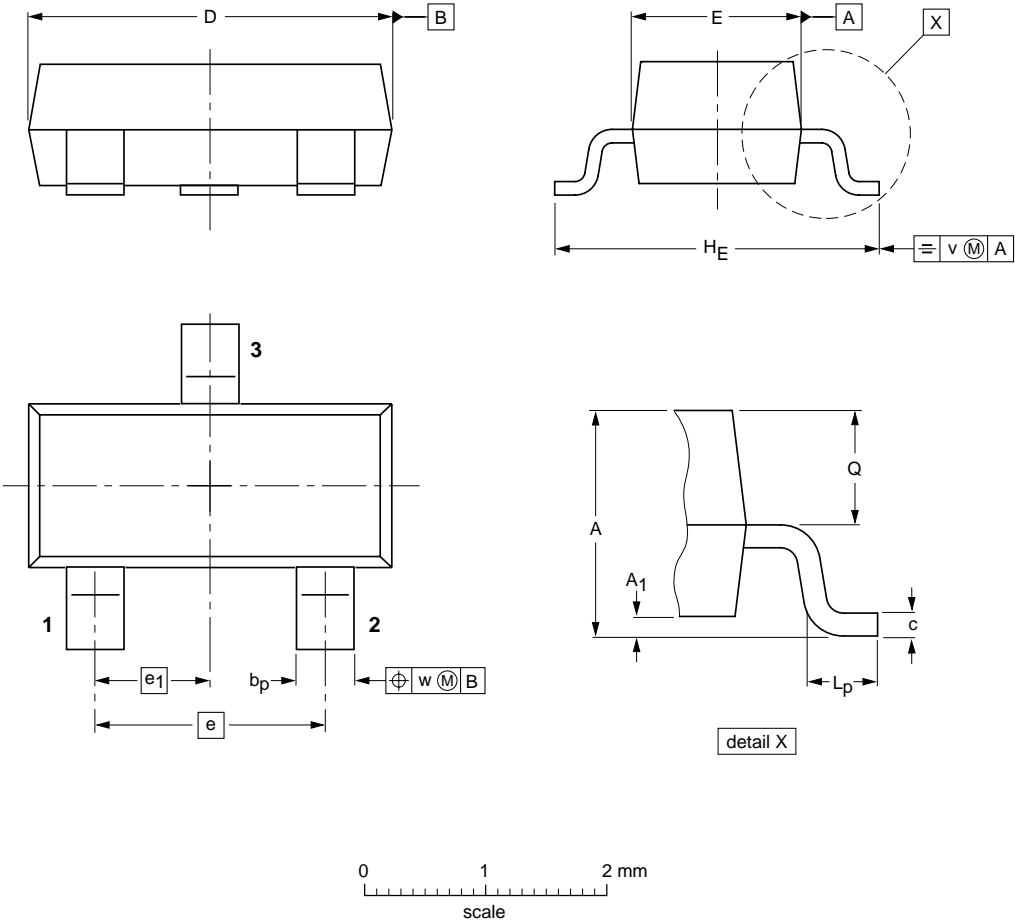
PNP resistor-equipped transistors;  
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PDTA143Z series

PACKAGE OUTLINES

Plastic surface-mounted package; 3 leads

SOT23



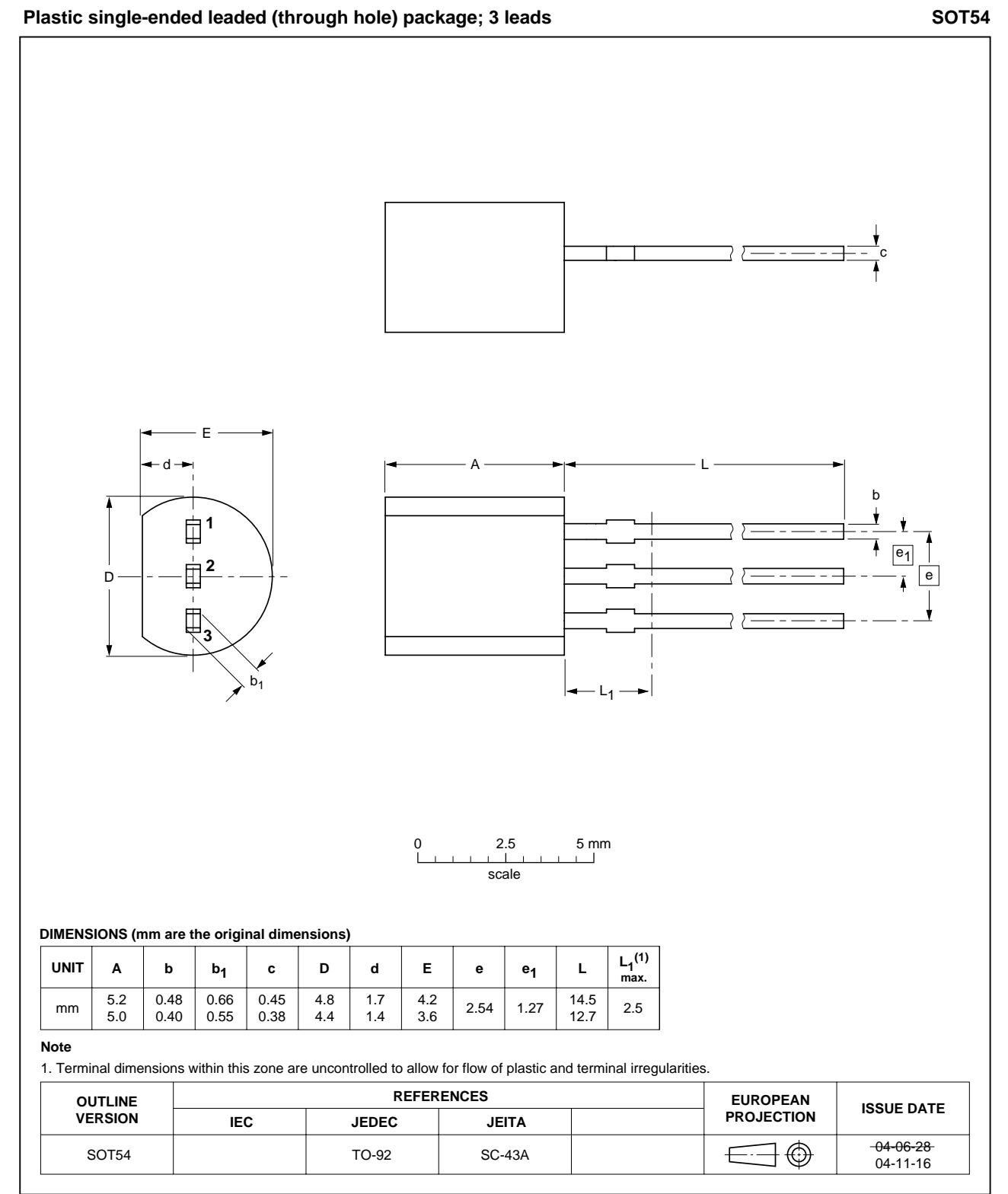
DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

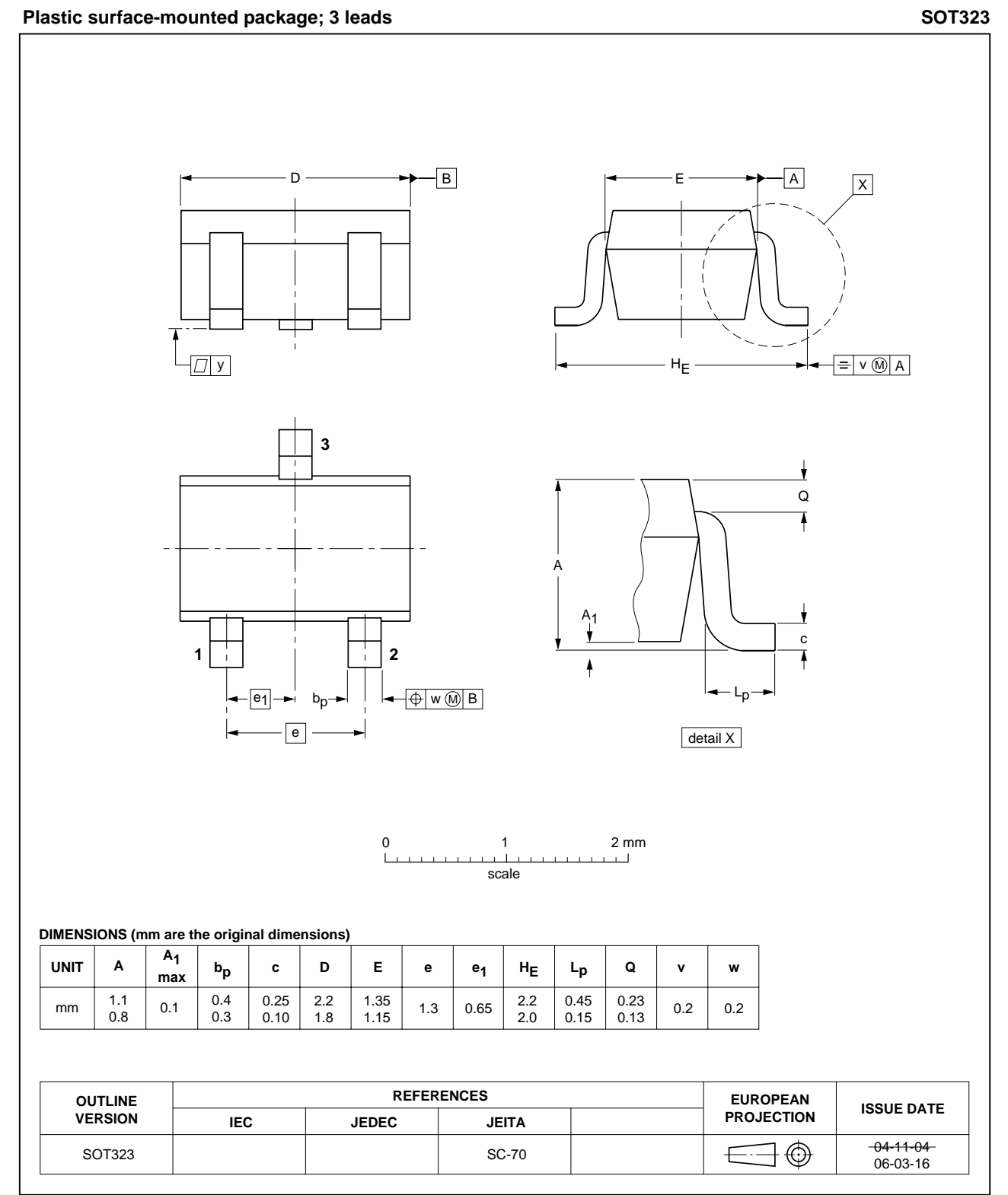
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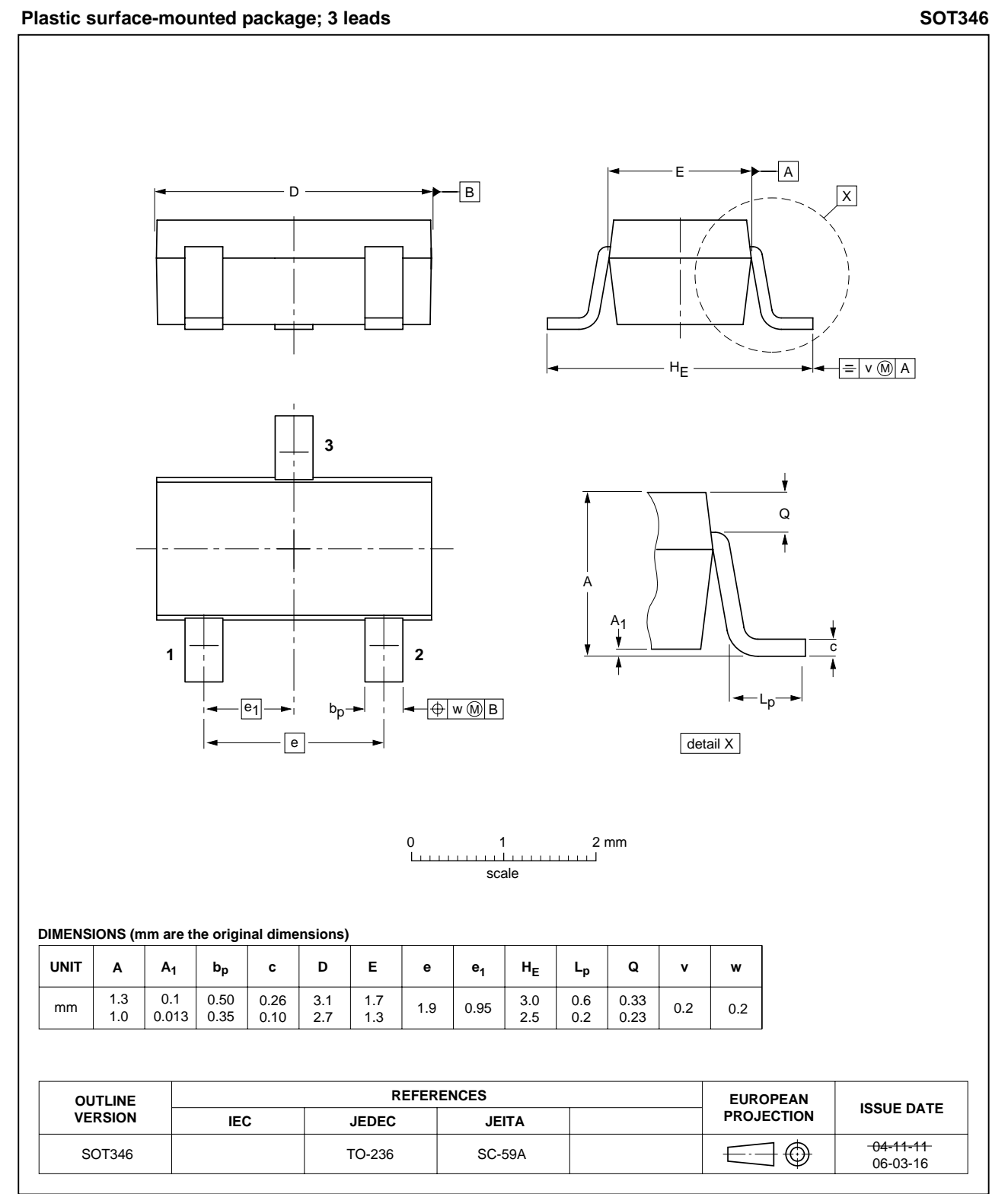
PDTA143Z series





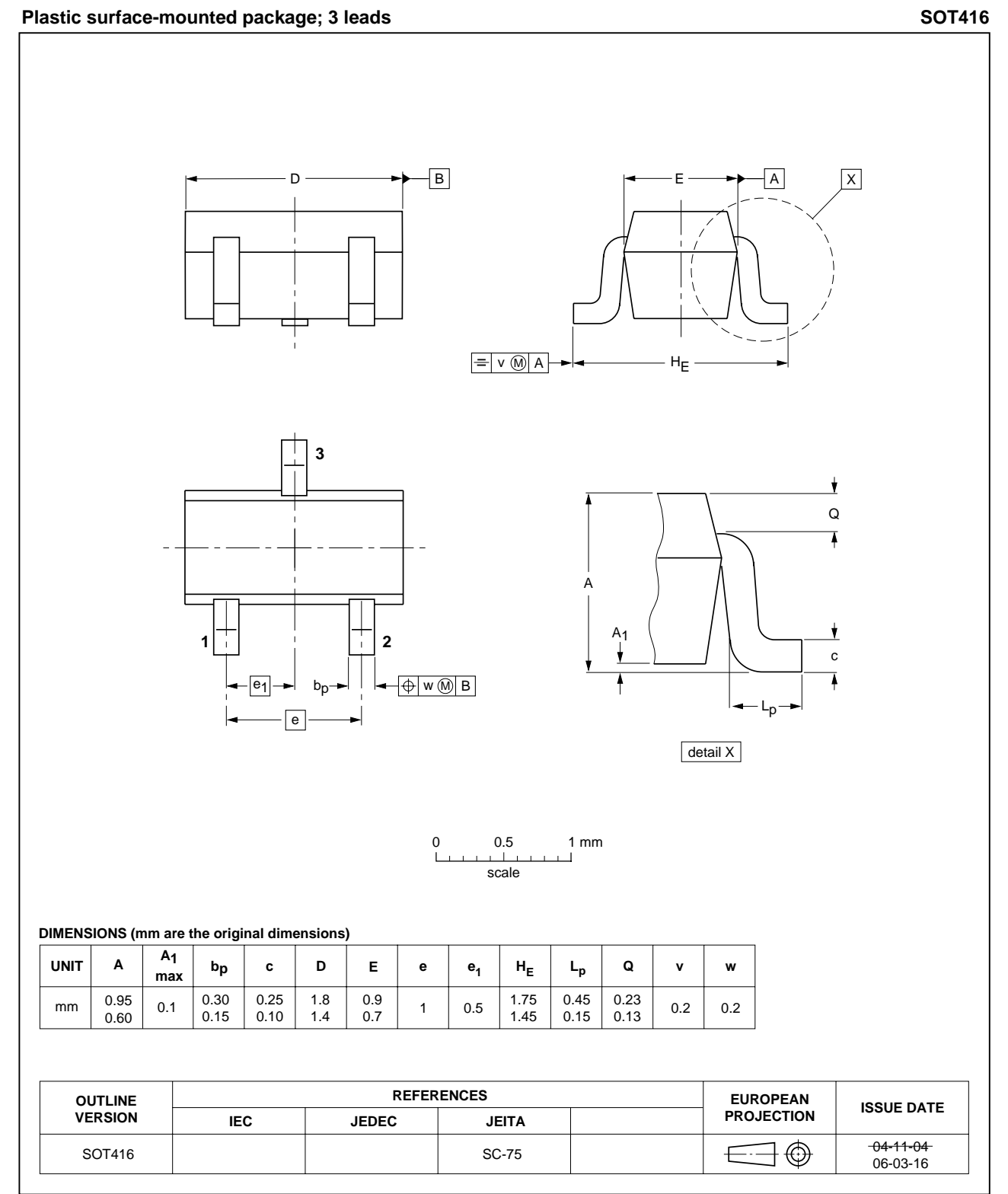
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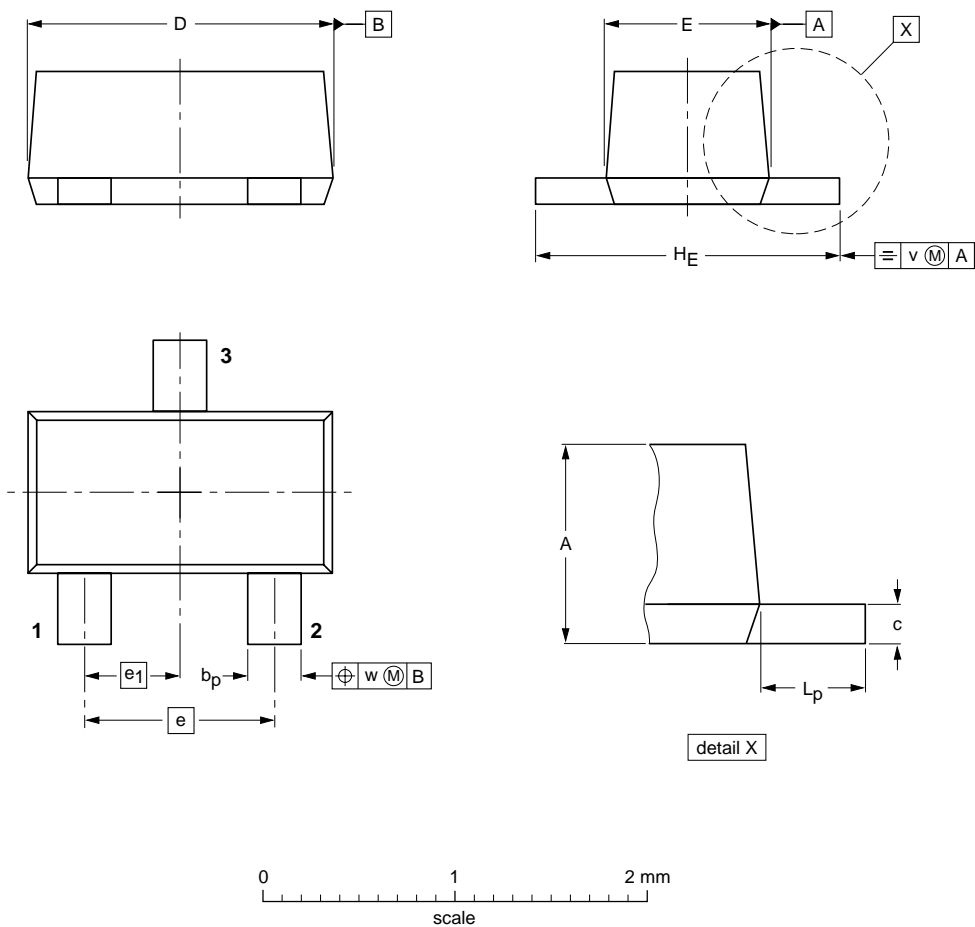


PNP resistor-equipped transistors;  
R1 = 4.7 kΩ, R2 = 47 kΩ

PDTA143Z series


Plastic surface-mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

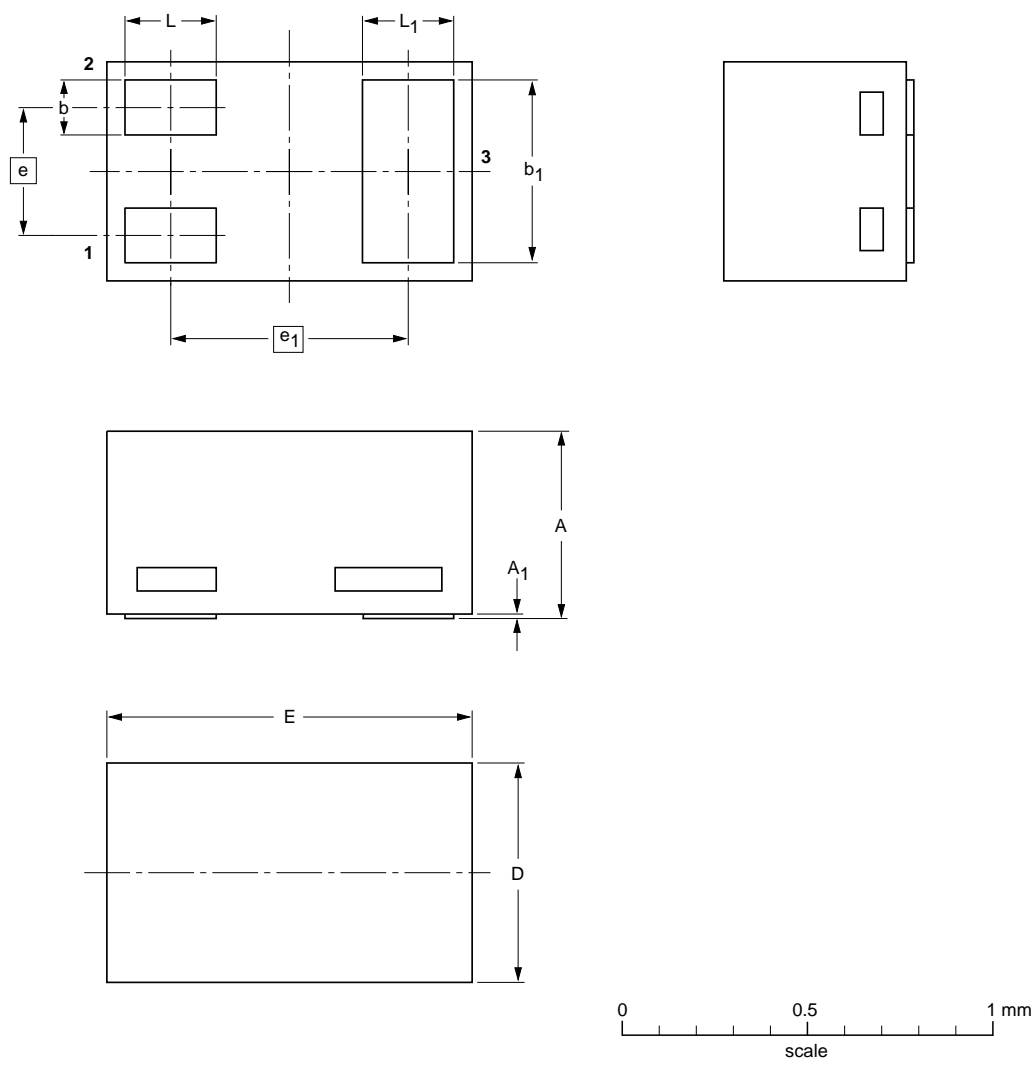
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT490			SC-89			05-07-28 06-03-16

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PDTA143Z series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note  
1. Including plating thickness

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT883			SC-101			03-02-05 03-04-03

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PDTA143Z series

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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